

1.1 Scope.

This specification covers the detail requirements for a monolithic CMOS 12×12-bit digital multiplier/accumulator integrated circuit.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number ¹
–1	ADSP-1009AS(X)/883B
–2	ADSP-1009AT(X)/883B

NOTE

¹See paragraph 1.2.3 for package identifier.

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline:

(X)	Package	Description
D	D-64A	64-Pin DIP
E	E-68A	68-Contact LCC
G	G-68A	68-Lead Pin Grid Array

1.3 Absolute Maximum Ratings.

Supply Voltage	–0.3 V to 7 V
Input Voltage	–0.3 V to V_{DD}
Output Voltage	–0.3 V to V_{DD}
Operating Temperature Range (Ambient)	–55°C to +125°C
Storage Temperature Range	–65°C to +150°C
Lead Temperature (Soldering 10 sec)	+300°C

1.5 Thermal Characteristics.

Thermal Resistance θ_{JC} : see MIL-M-38510, Appendix C.

ADSP-1009A – SPECIFICATIONS

Test	Symbol	Device	Design Limit @ +25°C	Sub Group 1	Sub Group 2, 3	Sub Group 9	Sub Group 10, 11	Test Condition ¹	Units
Digital Input High Voltage	V _{IH}	–1, 2	2.0	2.0	2.0			V _{DD} = max	V min
Digital Input Low Voltage	V _{IL}	–1, 2	0.8	0.8	0.8			V _{DD} = min	V max
Digital Output High Voltage	V _{OH}	–1, 2	2.4	2.4	2.4			V _{DD} = min I _{OH} = –0.4 mA	V min
Digital Output Low Voltage*	V _{OL}	–1, 2	0.4	0.6	0.6			V _{DD} = min I _{OL} = +4 mA	V max
Digital Input High Current	I _{IH}	–1, 2	10	10	10			V _{DD} = max V _{IN} = +5.0 V	μA max
Digital Input Low Current	I _{IL}	–1, 2	10	10	10			V _{DD} = max V _{IN} = 0.0 V	μA max
Three-State Leakage Current Low	I _{OZL}	–1, 2	50	50	50			V _{DD} = max V _{IL} = 0 V (High Z)	μA max
Three-State Leakage* Current High	I _{OZH}	–1, 2	50	50	50			V _{DD} = max V _{IH} = 0 V (High Z)	μA max
Supply Current*	I _{DD1}	–1, 2	70	75	75			V _{DD} = max; TTL Inputs; f = max	mA max
	I _{DD2}	–1, 2	35	40	40			V _{DD} = max All V _{IN} = 2.4 V	mA max
Output Delay*	t _D	–1, 2	35			40	40	Note 2	ns max
Three-State Enable* (High Z to High or Low)	t _{ENA}	–1, 2	30			35	35	Notes 2 and 3	ns max
Three-State Disable* (High or Low to High Z)	t _{DIS}	–1, 2	20			30	30	Notes 2 and 3	ns max
Input Setup Time*	t _S	–1, 2	20			20	20	Note 2	ns min
Clock Pulse Width*	t _{PW}	–1, 2	15			25	25	Note 2	ns min
Input Hold Time*	t _H	–1, 2	2			3	3	Note 2	ns min
Multiply/Accumulate Time*	t _{MAC}	–1	85			105	105	Note 2	ns max
		–2	70			90	90		

NOTES

*Indicates that a limit for this parameter has changed from REV. D.

¹T_A = +25°C; V_{DD} = +4.5 V min to +5.5 V max (unless otherwise noted).

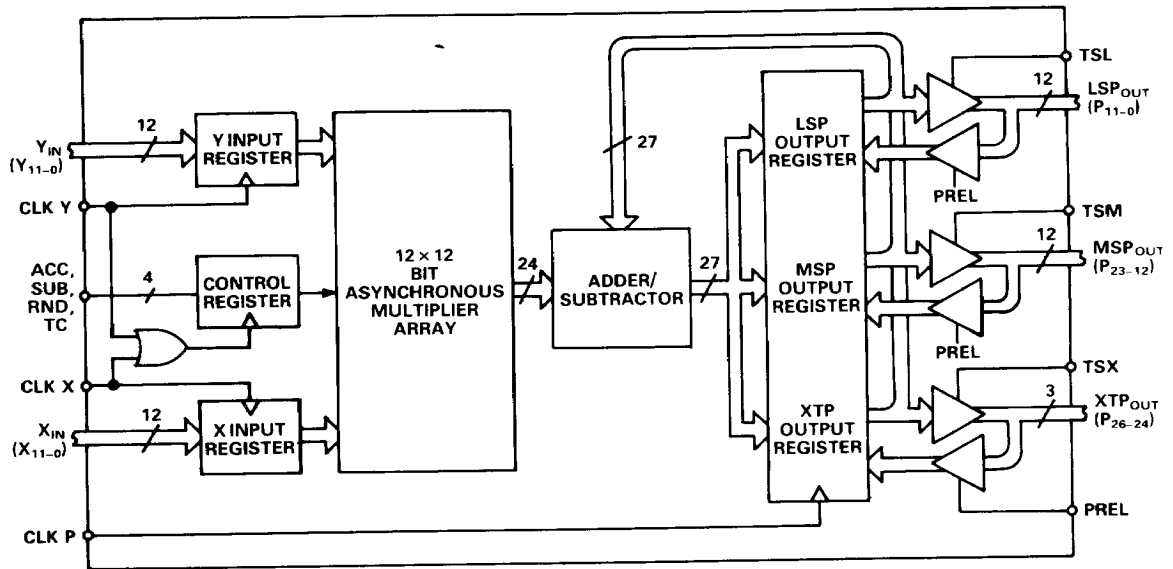
²TTL inputs of 0.3 V; V_{DD} = +4.5 V, rise time = 5 ns, and timing transitions, per Figure 1, measured at +1.5 V (unless otherwise noted).

³Transitions measured per Figure 2.

Table 1.

REV. E

3.2.1 Functional Block Diagram and Terminal Assignments.



Pin Assignments

DIP

PIN	FUNCTION	PIN	FUNCTION
1	X4	33	P19
2	X3	34	P20
3	X2	35	P21
4	X1	36	P22
5	X0	37	P23
6	ACC	38	P24
7	SUB	39	P25
8	RND	40	P26
9	TSL	41	TSX
10	P0	42	TC
11	P1	43	Y11
12	P2	44	Y10
13	P3	45	Y9
14	P4	46	Y8
15	P5	47	Y7
16	GND	48	Y6
17	P6	49	V _{DD}
18	P7	50	Y5
19	P8	51	Y4
20	P9	52	Y3
21	P10	53	Y2
22	P11	54	Y1
23	CLKP	55	Y0
24	PREL	56	CLKY
25	TSM	57	CLKX
26	P12	58	X11
27	P13	59	X10
28	P14	60	X9
29	P15	61	X8
30	P16	62	X7
31	P17	63	X6
32	P18	64	X5

Pin Grid Array

PIN	FUNCTION	PIN	FUNCTION
1	TSL	35	TSX
2	P0	36	TC
3	P1	37	Y11
4	P2	38	Y10
5	P3	39	Y9
6	P4	40	Y8
7	P5	41	Y7
8	GND	42	Y6
9	P6	43	V _{DD}
10	P7	44	Y5
11	P8	45	Y4
12	P9	46	Y3
13	P10	47	Y2
14	P11	48	Y1
15	CLKP	49	Y0
16	PREL	50	CLKY
17	N/C	51	N/C
18	TSM	52	CLKX
19	P12	53	X11
20	P13	54	X10
21	P14	55	X9
22	P15	56	X8
23	P16	57	X7
24	P17	58	X6
25	P18	59	X5
26	P19	60	X4
27	P20	61	X3
28	P21	62	X2
29	P22	63	X1
30	P23	64	X0
31	P24	65	ACC
32	P25	66	SUB
33	P26	67	RND
34	N/C	68	N/C

LCC

PIN	FUNCTION	PIN	FUNCTION
1	X4	35	P19
2	X3	36	P20
3	X2	37	P21
4	X1	38	P22
5	X0	39	P23
6	ACC	40	P24
7	SUB	41	P25
8	RND	42	P26
9	N/C	43	N/C
10	TSL	44	TSX
11	P0	45	TC
12	P1	46	Y11
13	P2	47	Y10
14	P3	48	Y9
15	P4	49	Y8
16	P5	50	Y7
17	GND	51	Y6
18	P6	52	V _{DD}
19	P7	53	Y5
20	P8	54	Y4
21	P9	55	Y3
22	P10	56	Y2
23	P11	57	Y1
24	CLKP	58	Y0
25	PREL	59	CLKY
26	N/C	60	N/C
27	TSM	61	CLKX
28	P12	62	X11
29	P13	63	X10
30	P14	64	X9
31	P15	65	X8
32	P16	66	X7
33	P17	67	X6
34	P18	68	X5

3.2.4 Microcircuit Technology Group.

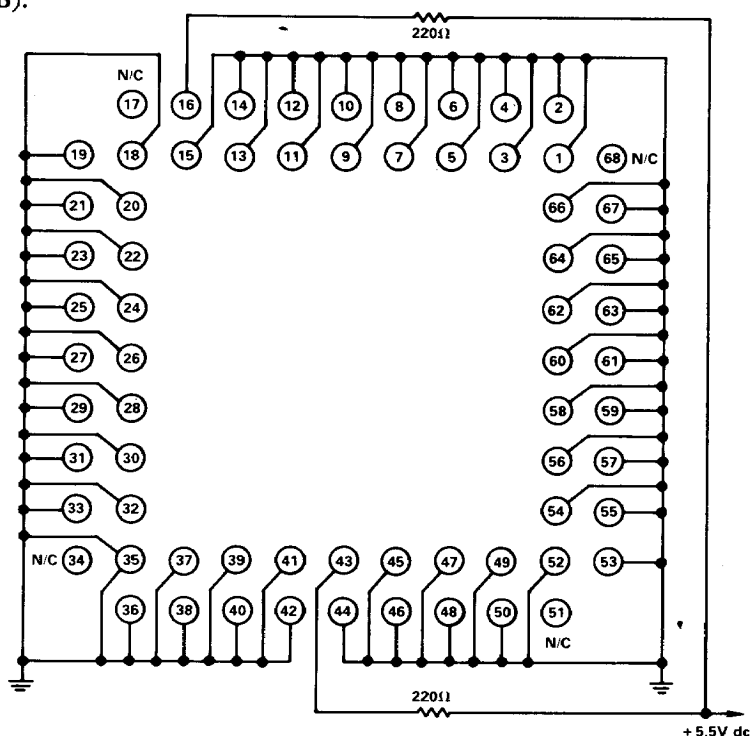
This microcircuit is covered by technology group (105).

REV. E

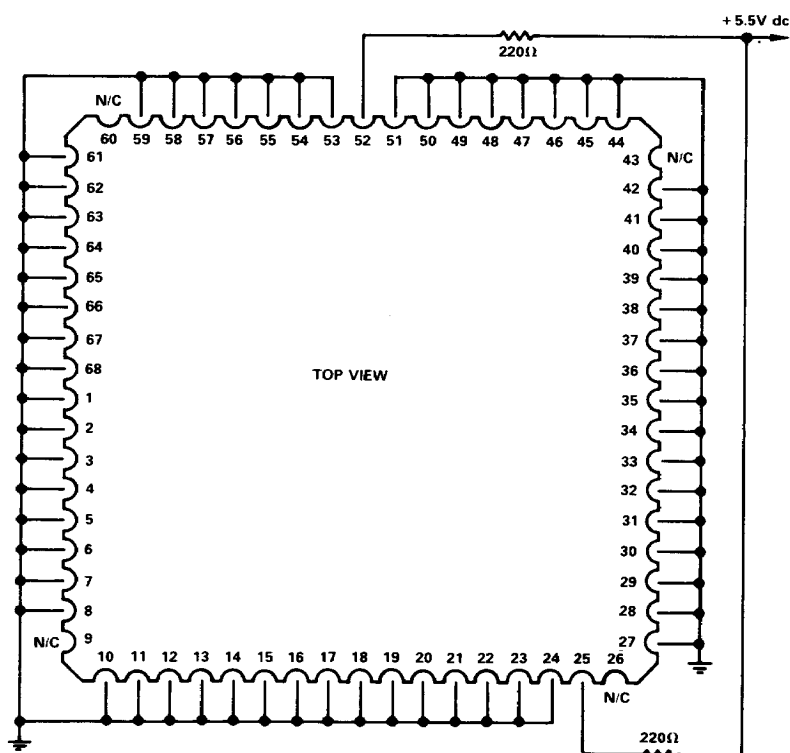
ADSP-1009A

4.2.1 Life Test/Burn-In Circuit.

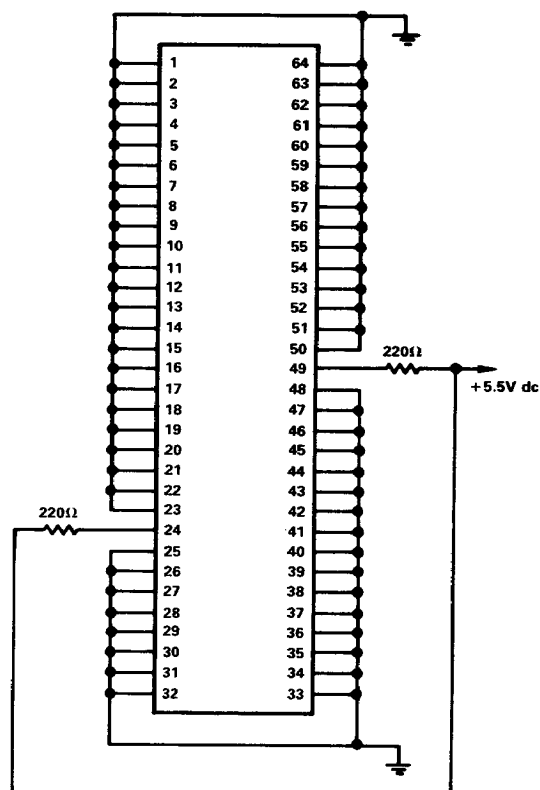
Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



ADSP-1009AG Life Test and Burn-In Circuit



ADSP-1009AE Life Test and Burn-In Circuit



ADSP-1009AD Life Test and Burn-In Circuit

REV. E

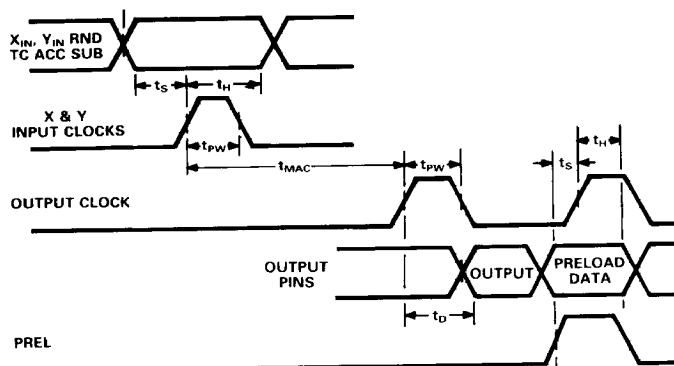


Figure 1. ADSP-1009A Timing Diagram

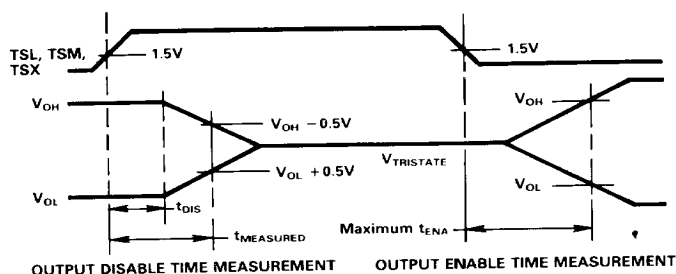


Figure 2. Three-State Disable and Enable Timing

Output disable time, t_{DIS} , is measured from the time the output enable control signal reaches 1.5 V to the time when all outputs have ceased driving. This is calculated by measuring the time, $t_{MEASURED}$, from the same starting point to when the output voltages have changed by 0.5 V toward +1.5 V. From the tester capacitive loading, C_L , and the measured current, i_L , the decay time, t_{DECAY} , can be approximated to first order by:

$$t_{DECAY} = \frac{C_L \cdot 0.5 V}{i_L}$$

from which

$$t_{DIS} = t_{MEASURED} - t_{DECAY}$$

is calculated. Disable times are longest at the highest specified temperature.

The maximum output enable time, maximum t_{ENA} , is also measured from output enable control signal at 1.5 V to the time when all outputs have reached TTL input levels (V_{OH} or V_{OL}). This could also be considered as "data valid." Maximum enable times are longest at the highest specified temperature.

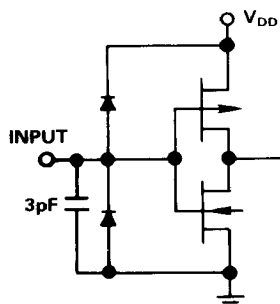


Figure 3. Equivalent Input Circuit

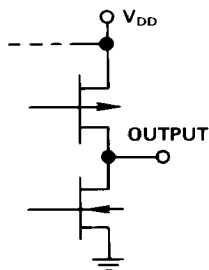


Figure 4. Equivalent Output Circuit

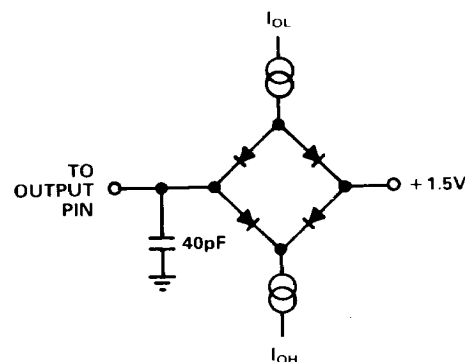


Figure 5. Normal Load Circuit for AC Measurements

REV. E

ACC	SUB	Function
1	1	$\text{Accumulator}_t = X_t \cdot Y_t - \text{Accumulator}_{t-1}$
1	0	$\text{Accumulator}_t = X_t \cdot Y_t + \text{Accumulator}_{t-1}$
0	X	$\text{Accumulator}_t = X_t \cdot Y_t$

Table 2. Function Truth Table

PREL	TSX	TSM	TSL	XTP	MSP	LSP
0	0	0	0	Q	Q	Q
0	0	0	1	Q	Q	Z
0	0	1	0	Q	Z	Q
0	0	1	1	Q	Z	Z
0	1	0	0	Z	Q	Q
0	1	0	1	Z	Q	Z
0	1	1	0	Z	Z	Q
0	1	1	1	Z	Z	Z
1	0	0	0	Z	Z	Z
1	0	0	1	Z	Z	Preload
1	0	1	0	Z	Preload	Z
1	0	1	1	Z	Preload	Preload
1	1	0	0	Preload	Z	Z
1	1	0	1	Preload	Z	Preload
1	1	1	0	Preload	Preload	Z
1	1	1	1	Preload	Preload	Preload

NOTE:

Z = Output buffers at high impedance (output disabled)

Q = Output buffers at low impedance. Contents of output register will be transferred to output pins.

Preload = Output buffers at high impedance, or output disabled. Preload data (PD) supplied externally at output pins will be loaded into the output register at the rising edge of CLK P.

Table 3. Preload Truth Table